

NPN Darlington Transistor

PZTA28, MMBTA28

Description

This device is designed for applications requiring extremely high current gain at collector currents to 500 mA. Sourced from process 03.

Features

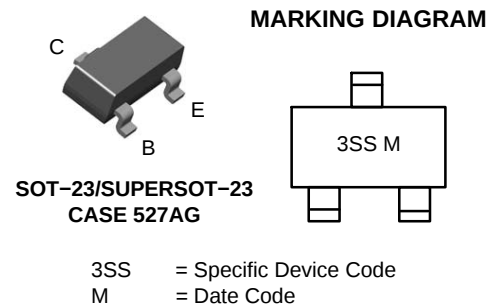
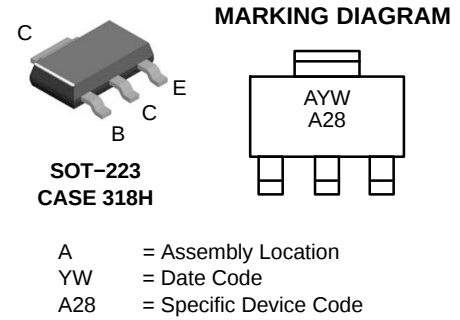
- These are Pb-Free Devices

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Note 1, Note 2)

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	80	V
V_{CBO}	Collector-Base Voltage	80	V
V_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current – Continuous	800	mA
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are based on a maximum junction temperature of 150°C .
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.



ORDERING INFORMATION

Device	Package	Shipping [†]
PZTA28	SOT-223	4000 / Tape & Reel
MMBTA28	SOT-23	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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THERMAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Max		Unit
		PZTA28 (Note 3)	MMBTA28 (Note 4)	
P_D	Total Device Dissipation	1000	350	mW
	Derate Above 25°C	8.0	2.8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	125	357	$^\circ\text{C/W}$

3. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

4. Device mounted on FR-4 PCB 36 mm x 18 mm x 1.5 mm; mounting pad for the collector lead minimum 6cm².

ELECTRICAL CHARACTERISTICS (Note 5) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Max	Unit
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_C = 100\ \mu\text{A}$, $V_{BE} = 0$	80		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\ \mu\text{A}$, $I_E = 0$	80		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\ \mu\text{A}$, $I_C = 0$	12		V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 60\ \text{V}$, $I_E = 0$		100	nA
I_{CES}	Collector Cut-Off Current	$V_{CE} = 60\ \text{V}$, $V_{BE} = 0$		500	nA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 10\ \text{V}$, $I_C = 0$		100	nA
h_{FE}	DC Current Gain	$I_C = 10\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$	10000		
		$I_C = 100\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$	10000		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10\ \text{mA}$, $I_B = 0.01\ \text{mA}$		1.2	V
		$I_C = 100\ \text{mA}$, $I_B = 0.1\ \text{mA}$		1.5	
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 100\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$		2.0	V
f_T	Current Gain – Bandwidth Product	$I_C = 15\ \text{mA}$, $V_{CE} = 5.0\ \text{V}$, $f = 100\ \text{MHz}$	125		MHz
C_{obo}	Output Capacitance	$V_{CB} = 1.0\ \text{V}$, $I_E = 0$, $f = 1.0\ \text{MHz}$		8.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2.0\%$.

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TYPICAL PERFORMANCE CHARACTERISTICS

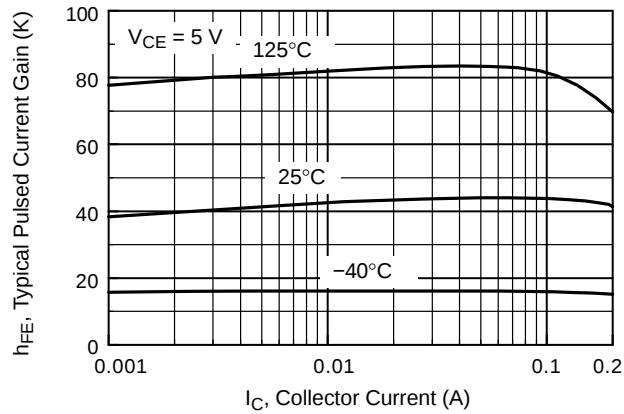


Figure 1. Typical Pulsed Current Gain vs. Collector Current

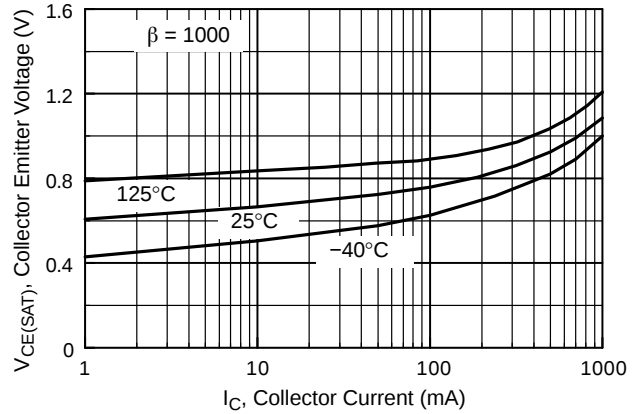


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

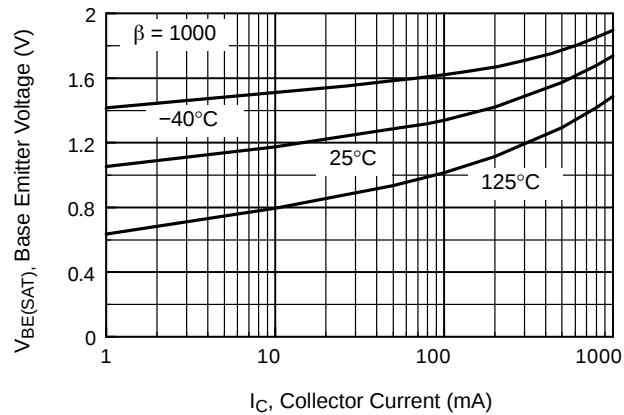


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

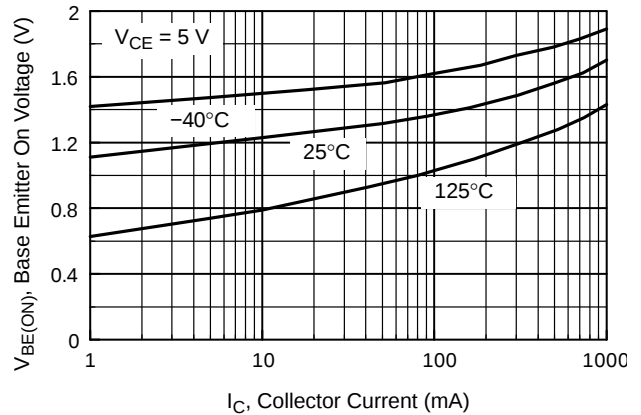


Figure 4. Base-Emitter On Voltage vs. Collector Current

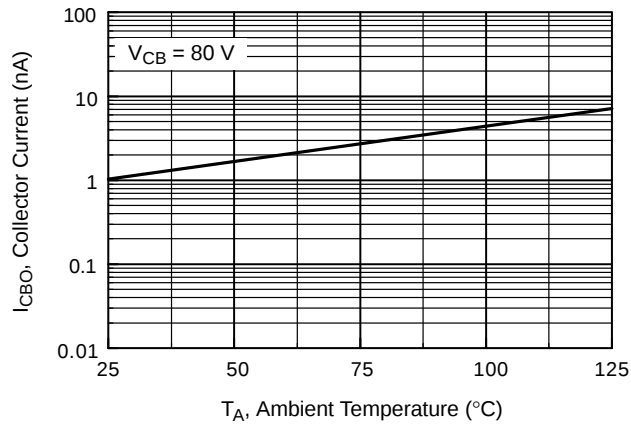


Figure 5. Collector Cut-Off Current vs. Ambient Temperature

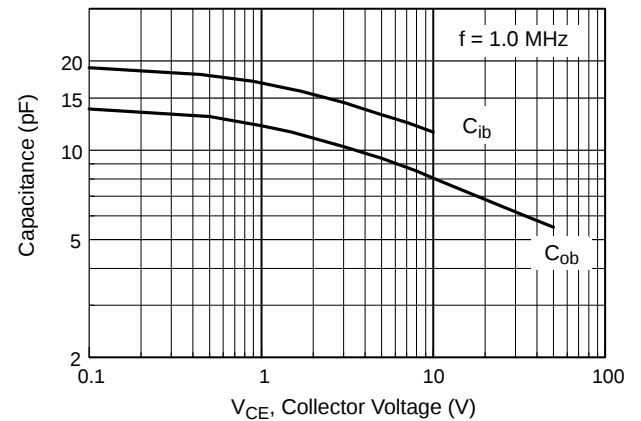


Figure 6. Input and Output Capacitance vs. Reverse Voltage

PZTA28, MMBTA28

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

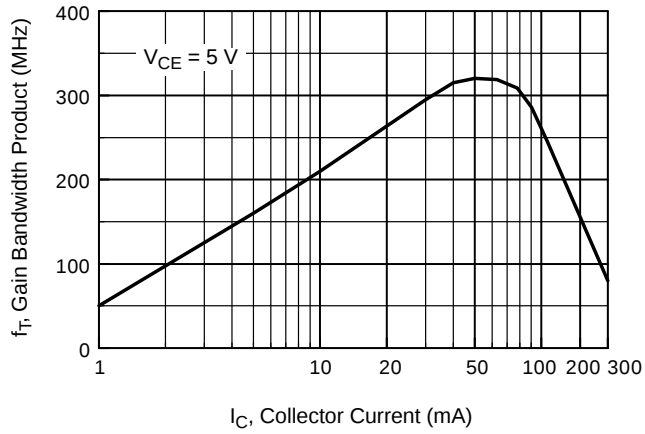


Figure 7. Gain Bandwidth Product vs. Collector Current

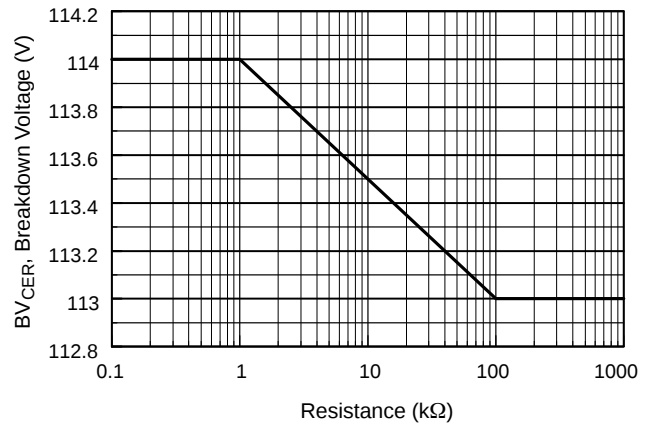


Figure 8. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

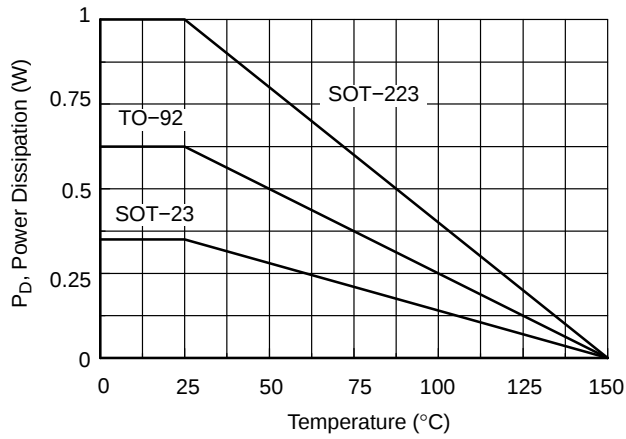
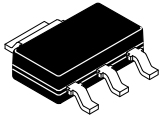


Figure 9. Power Dissipation vs. Ambient Temperature



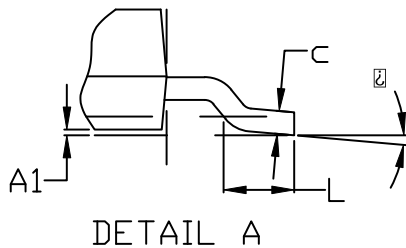
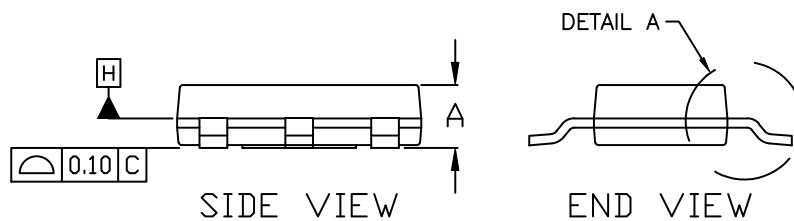
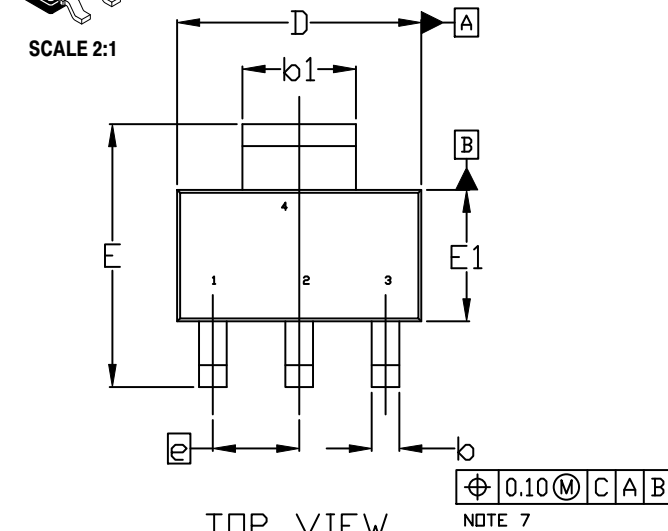
SCALE 2:1

SOT-223
CASE 318H
ISSUE B

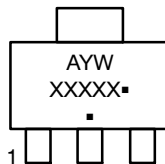
DATE 13 MAY 2020

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E1 ARE DETERMINED AT DATUM H. DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. SHALL NOT EXCEED 0.23mm PER SIDE.
4. LEAD DIMENSIONS b AND b1 DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS 0.08mm PER SIDE.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
7. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.



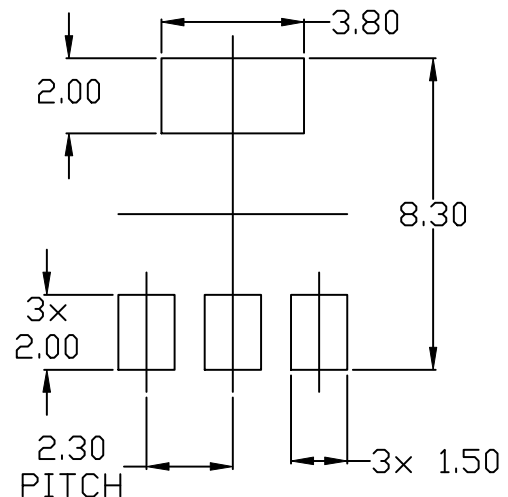
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.80
A1	0.02	0.06	0.11
b	0.60	0.74	0.88
b1	2.90	3.00	3.10
c	0.24	---	0.35
D	6.30	6.50	6.70
E	6.70	7.00	7.30
E1	3.30	3.50	3.70
e	2.30 BSC		
L	0.25	---	---
⌀	0°	---	10°

GENERIC MARKING DIAGRAM*


A = Assembly Location
Y = Year
W = Work Week
XXXXX = Specific Device Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

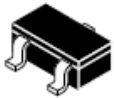
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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SOT-23/SUPERSOT™ –23, 3 LEAD, 1.4x2.9
CASE 527AG
ISSUE A

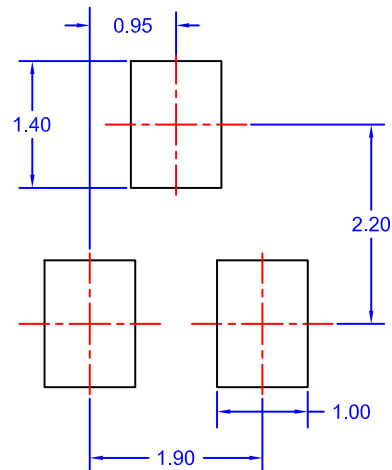
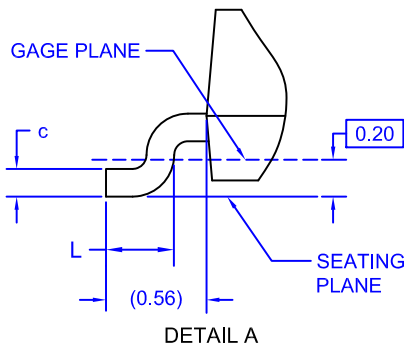
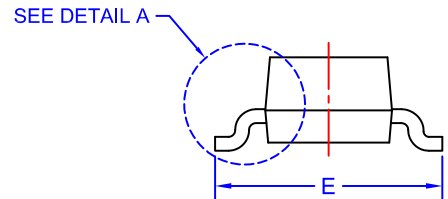
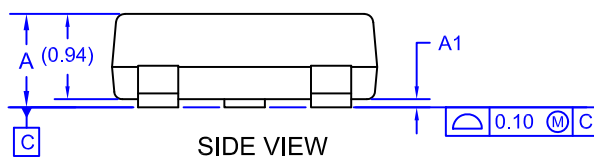
DATE 09 DEC 2019



NOTES: UNLESS OTHERWISE SPECIFIED

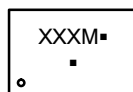
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2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.

DIM	MIN.	NOM.	MAX.
A	0.85	0.95	1.12
A1	0.00	0.05	0.10
b	0.370	0.435	0.508
c	0.085	0.150	0.180
D	2.80	2.92	3.04
E	2.31	2.51	2.71
E1	1.20	1.40	1.52
e	0.95 BSC		
e1	1.90 BSC		
L	0.33	0.38	0.43



*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Month Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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